# 3.3 V, 2 Channel, 2:1 Differential Mux/Demux

The NL3HS3124A is a 2 channel, 2-to-1 differential multiplexer / demultiplexer for USB 3.0, PCI Express Generation 3, or other high-speed serial interface applications. The NL3HS3124A can switch two differential signals to one of two locations. The device has minimal channel-to-channel skew as well as minimal channel-to-channel crosstalk, making the device ideal for high-speed serial interface applications.

#### **Features**

- 2 Bidirectional Channel, 2: 1 Differential Multiplexer/Demultiplexer
- High-speed Signal Switching for 8 Gbps Applications
- High Bandwidth: > 6.3 GHz at -3 dB
- Low Insertion Loss:
  - ◆ -0.5 dB at 100 MHz
  - ◆ -2.8 dB at 4.0 GHz
- Low Return Loss: -9.27 dB at 4 GHz
- Low Crosstalk: -35 dB at 4 GHz
- Low Off-state Isolation: -19 dB at 4 GHz
- Low Intra-pair Skew: 5 ps Typical
- Low Inter-pair Skew: 35 ps Maximum
- V<sub>DD</sub> Operating Range: 3.0 V to 3.6 V
- Shutdown Pin (SD) for Power–saving Mode
- $\bullet \;$  Standby Current less than 1  $\mu A$
- ESD Tolerance:
  - ◆ 4000 V HBM
  - ◆ 300 V MM
  - ◆ 2000 V CDM
- 2.5 mm x 4.5 mm QFN20 Package
- This Device is Pb–Free, Halogen–Free/BFR–Free and is RoHS–Compliant

## **Applications**

- Routing of High-speed Differential Signals
  - ♦ USB 3.0
  - ◆ PCIe Gen3
  - DisplayPort 1.2
  - SATA 6 Gbps



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QFN20 MN SUFFIX CASE 485AA

#### **MARKING DIAGRAM**

1 0 3HS3 124A ALYW

3HS3124A = Specific Device Code

A = Assembly Location L = Wafer Lot Y = Year

W = Work Week ■ Pb-Free Package

(Note: Microdot may be in either location)

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NL3HS3124AMNTWG	QFN20 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

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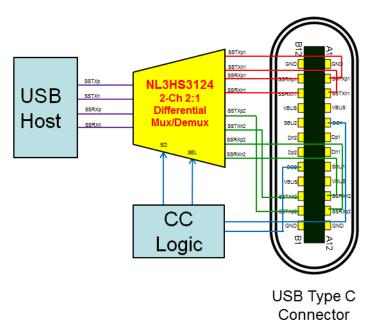


Figure 1. Typical Application

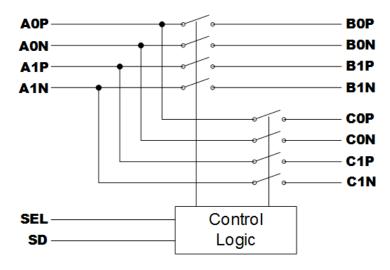


Figure 2. Block Diagram

**Table 1. FUNCTION TABLE** 

SD	SEL	Function
L	L	An connected to Bn
L	Н	An connected to Cn
Н	X	An, Bn and Cn in Hi–Z, Device in Shutdown

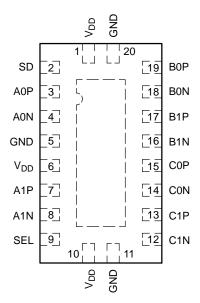


Figure 3. Pinout (Top Through View)

**Table 2. PIN ASSIGNMENT** 

Pin Name	Pin	Туре	Description
A0P	3	I/O	Channel 0, Port A Differential Signal I/O
AON	4	I/O	
A1P	7	I/O	Channel 1, Port A Differential Signal I/O
A1N	8	I/O	
B0P	19	I/O	Channel 0, Port B Differential Signal I/O
B0N	18	I/O	
B1P	17	I/O	Channel 1, Port B Differential Signal I/O
B1N	16	I/O	
C0P	15	I/O	Channel 0, Port C Differential Signal I/O
C0N	14	I/O	
C1P	13	I/O	Channel 1, Port C Differential Signal I/O
C1N	12	I/O	
SEL	9	Input (CMOS)	Mux/Demux Select Pin
SD	2	Input (CMOS)	Shutdown Pin
$V_{DD}$	1, 6, 10	Power	Power
GND	5, 11, 20, Center Pad	Power	Ground

**Table 3. MAXIMUM RATINGS** 

Symbol	Rating		Value	Unit
$V_{DD}$	Positive DC Supply Voltage		-0.5 to +4.6	V
V <sub>IN</sub>	Digital Control Input Voltage (SEL, SD)		-0.5 to V <sub>DD</sub> +0.5	V
Ts	Storage Temperature		-65 to +150	°C
ESD	ESD Performance			V
	HBM (JESD22-A114)	All Pins	4000	
	MM (JESD22-A115-A)	All Pins	300	
	CDM (JESD22-C101)	All Pins	2000	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

**Table 4. RECOMMENDED OPERATING CONDITIONS** 

Symbol	Parameter		Тур	Max	Unit
$V_{DD}$	Positive DC Supply Voltage	3.0	3.3	3.6	V
$V_{IN}$	Digital Control Input Voltage (SEL, SD) (Note 1)	0		$V_{DD}$	V
V <sub>IS</sub>	Differential Pin Input Voltage (An, Bn, Cn)	0		2.4	V
$V_{IC}$	Common-Mode Input Voltage (An, Bn, Cn)	0		2	V
$V_{ID}$	Differential Input Voltage (An, Bn, Cn), peak-to-peak	0		1.6	V
T <sub>A</sub>	Operating Temperature	-40		85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## **Table 5. DC ELECTRICAL CHARACTERISTICS**

Voltages referenced to GND. All typical values are at  $T_A = 25$ °C unless otherwise specified.

				$T_A = -40^{\circ}C$ to $+85^{\circ}C$			
Symbol	Parameter	Conditions	V <sub>CC</sub> (V)	Min	Тур	Max	Unit
$V_{IH}$	Input Voltage High	SEL, SD	3.0 - 3.6	2.0			V
$V_{IL}$	Input Voltage Low	SEL, SD	3.0 - 3.6			0.5	V
I <sub>IN</sub>	Input Leakage Current	SEL, SD: $V_{IN} = 0 \text{ V or } V_{DD}$	3.6			±5	μΑ
I <sub>IS</sub>	Switch Input Leakage Current	An, Bn, Cn: $V_{IS} = 0 \text{ V or } 2.4 \text{ V}$	3.6			±10	μΑ
I <sub>DD</sub>	Supply Current	Operating mode: SD = L	3.6		0.2	1	mA
		Shutdown mode: SD = H	3.6			1	μΑ

<sup>1.</sup> Control input must be held High or Low. It must not float.

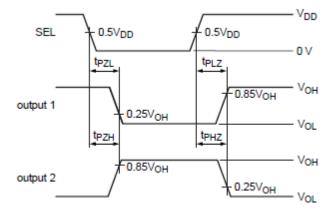
 $\textbf{Table 6. DYNAMIC CHARACTERISTICS} \ \ \text{Voltages referenced to GND. All typical values are at } \ T_{A} = 25^{\circ}\text{C unless otherwise specified.}$ 

				T <sub>A</sub> =	-40°C to +	85°C	
Symbol	Parameter	Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Unit
DDIL	Differential Insertion Loss	Channel OFF	3.0 – 3.6				dB
		f = 4 GHz			-19		
		f = 100 MHz			-47		
		Channel ON					
		f = 4 GHz			-2.8		
		f = 100 MHz			-0.5		
DDNEXT	Differential Near-End Crosstalk	Adjacent Channels ON	3.0 - 3.6				dB
		f = 4 GHz			-26		
		f = 100 MHz			-62		
BW	-3 dB Bandwidth		3.0 - 3.6		6.3		GHz
DDRL	Differential Return Loss	f = 4 GHz	3.0 – 3.6		-9.27		dB
		f = 100 MHz			-23.2		
R <sub>ON</sub>	Switch ON Resistance (Note 2)	$VIS = 2 \text{ V}, I_{IS} = 19 \text{ mA}$	3.3		6		Ω
C <sub>IO(ON)</sub>	ON-State Input/Output Capacitance	f = 2.5 GHz	3.0 – 3.6		2.03		pF

<sup>2.</sup> Measured by the voltage drop between A and B pins at the indicated current through the switch. ON resistance is determined by the lower of the voltage on the two (A or B ports).

 Table 7. SWITCHING CHARACTERISTICS
 All typical values are for  $V_{CC} = 3.3 \text{ V}$  at  $T_A = 25^{\circ}\text{C}$  unless otherwise specified.

				$T_A = -40^{\circ}C$ to $+85^{\circ}C$			
Symbol	Parameter	Condition	V <sub>CC</sub> (V)	Min	Тур	Max	Unit
tSTARTUP	Startup Time	Supply Voltage Valid, or SD going Low to channel specified operating conditions	3.0 – 3.6			10	ms
t <sub>PD</sub>	Propagation Delay	Port A to Port B or C, or vice-versa	3.0 – 3.6		60		ps
t <sub>PZH</sub>	OFF–State to High Propagation Delay		3.0 – 3.6			300	ns
t <sub>PZL</sub>	OFF-State to Low Propagation Delay		3.0 – 3.6			70	ns
t <sub>PHZ</sub>	High to OFF–State Propagation Delay		3.0 – 3.6			50	ns
t <sub>PLZ</sub>	Low to OFF–State Propagation Delay		3.0 – 3.6			50	ns
t <sub>sk(dif)</sub>	Differential Skew	Intra-pair	3.0 – 3.6		5		ps
t <sub>sk</sub>	Skew	Inter-pair	3.0 – 3.6			35	ps

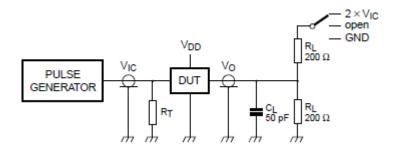


Output 1 is for an output with internal conditions such that the output is LOW except when disabled by the output control.

Output 2 is for an output with internal conditions such that the output is HIGH except when disabled by the output control.

The outputs are measured one at a time with one transition per measurement.

Figure 4. Voltage Waveforms, Enable and Disable Times



 $C_L$  = load capacitance; includes jig and probe capacitance.  $R_T$  = termination resistance; should be equal to  $Z_0$  of the pulse generator. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  5 MHz;  $Z_0$  = 50  $\Omega$ ;  $t_r$   $\leq$  2.5 ns;  $t_f$   $\leq$  2.5 ns.

Figure 5. Test Circuit for Switching Times

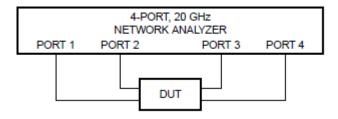


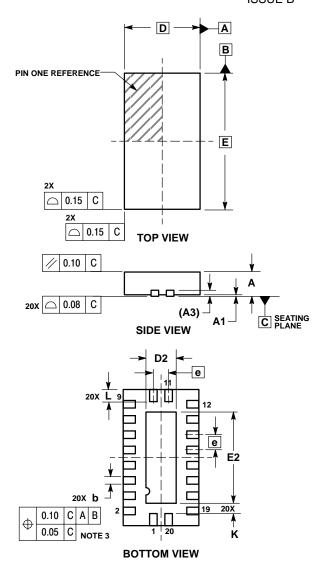
Figure 6. Test Circuit

Table 8. LOADING CONDITIONS FOR SWITCHING/TIMING TESTS

	Lo	Load		
Test	CL	R <sub>L</sub>	Switch	
t <sub>PLZ</sub> , t <sub>PZL</sub> (Output on B Side)	50 pF	200 Ω	2 x V <sub>IC</sub>	
t <sub>PHZ</sub> , t <sub>PZH</sub> (Output on B Side)	50 pF	200 Ω	GND	
t <sub>PD</sub>		200 Ω	Open	

#### PACKAGE DIMENSIONS

#### QFN20, 2.5x4.5 MM CASE 485AA **ISSUE B**



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: MILLIMETERS.
  DIMENSIONS & APPLIES TO PLATED
- TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL.
- COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.80	1.00			
A1	0.00	0.05			
A3	0.20	REF			
b	0.20	0.30			
D	2.50	BSC			
D2	0.85	1.15			
Е	4.50	BSC			
E2	2.85	3.15			
е	0.50	BSC			
K	0.20				
L	0.35	0.45			

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